

AMENDMENTS TO THE CLAIMS

Claims 1-8. (Canceled)

9. (Currently Amended) An apparatus for incorporating an impurity in a thin film on a substrate arranged in a deposition chamber comprising:
 - an impurity cell in the deposition chamber, the impurity cell comprising: having a pre-determined amount of an impurity in a confined volume;
 - wherein, the impurity is removed from the impurity cell in a gas phase and is delivered carrier-gas free to the thin film; further wherein the impurity in the gas phase is incorporated into the thin film during thin film deposition
 - a substantially solid material having exposed surfaces located entirely within the deposition chamber; and
 - an impurity-containing fluid adhered on said exposed surfaces.
10. (Original) The apparatus of claim 9, wherein the impurity is selected from the group consisting of carbon and germanium.
11. (Original) The apparatus of claim 9, wherein the thin film comprises epitaxial or polycrystalline silicon.
12. (Original) The apparatus of claim 11, wherein the impurity incorporated into the epitaxial or polycrystalline silicon thin film comprises carbon in a concentration from about 1E13 atoms/cm³ to a maximum solubility of carbon in the silicon thin film.

Claims 13-15 (Canceled).

16. (Original) The apparatus of claim 9, wherein the deposition chamber comprises a vacuum

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chamber.

Claims 17-32. (Canceled)

33. (New) The apparatus of claim 9, wherein the impurity-containing fluid comprises a liquid or a gas.
34. (New) The apparatus of claim 33, wherein the gas comprises methane, ethane, propane or butane.
35. (New) The apparatus of claim 33, wherein the liquid comprises a liquid alkane selected from pentane, hexane, heptane, octane, nonane, or the like.
36. (New) The apparatus of claim 9, wherein a layer of the impurity-containing fluid is adhered on said exposed surfaces.
37. (New) The apparatus of claim 9, wherein the substantially solid material comprises porous, curvaceous or pitted features.
38. (New) The apparatus of claim 9, wherein the substantially solid material comprises metal, ceramic, Teflon, stainless steel, alumina, silica or zirconia.
39. (New) The apparatus of claim 9 further comprising:
an enclosure in the deposition chamber, the impurity cell located in the enclosure;
and
an impurity source coupled to the enclosure.

40. (New) The apparatus of claim 39, wherein the enclosure and the impurity source are coupled by a connector.
41. (New) The apparatus of claim 40, wherein the connector includes a valve, wherein when the valve is in one state the enclosure and the impurity source are isolated, and when the valve is in another state the impurity cell can be charged by the impurity source.
42. (New) The apparatus of claim 39, wherein the impurity source is external to the deposition chamber.